

ABSTRACT OF THE DISCLOSURE

This invention includes methods of depositing silicon dioxide comprising layers in the fabrication of integrated circuitry, methods of forming trench isolation, and methods of forming bit line over capacitor arrays of memory cells. In one implementation, a semiconductor substrate having an exposed outer first surface comprising silicon-nitrogen bonds and an exposed outer second surface comprising at least one of silicon and silicon dioxide is provided. A layer comprising a metal is deposited over at least the outer second surface. A silanol is flowed to the metal of the outer second surface and to the outer first surface effective to selectively deposit a silicon dioxide comprising layer over the outer second surface as compared to the outer first surface. Other aspects and implementations are contemplated.